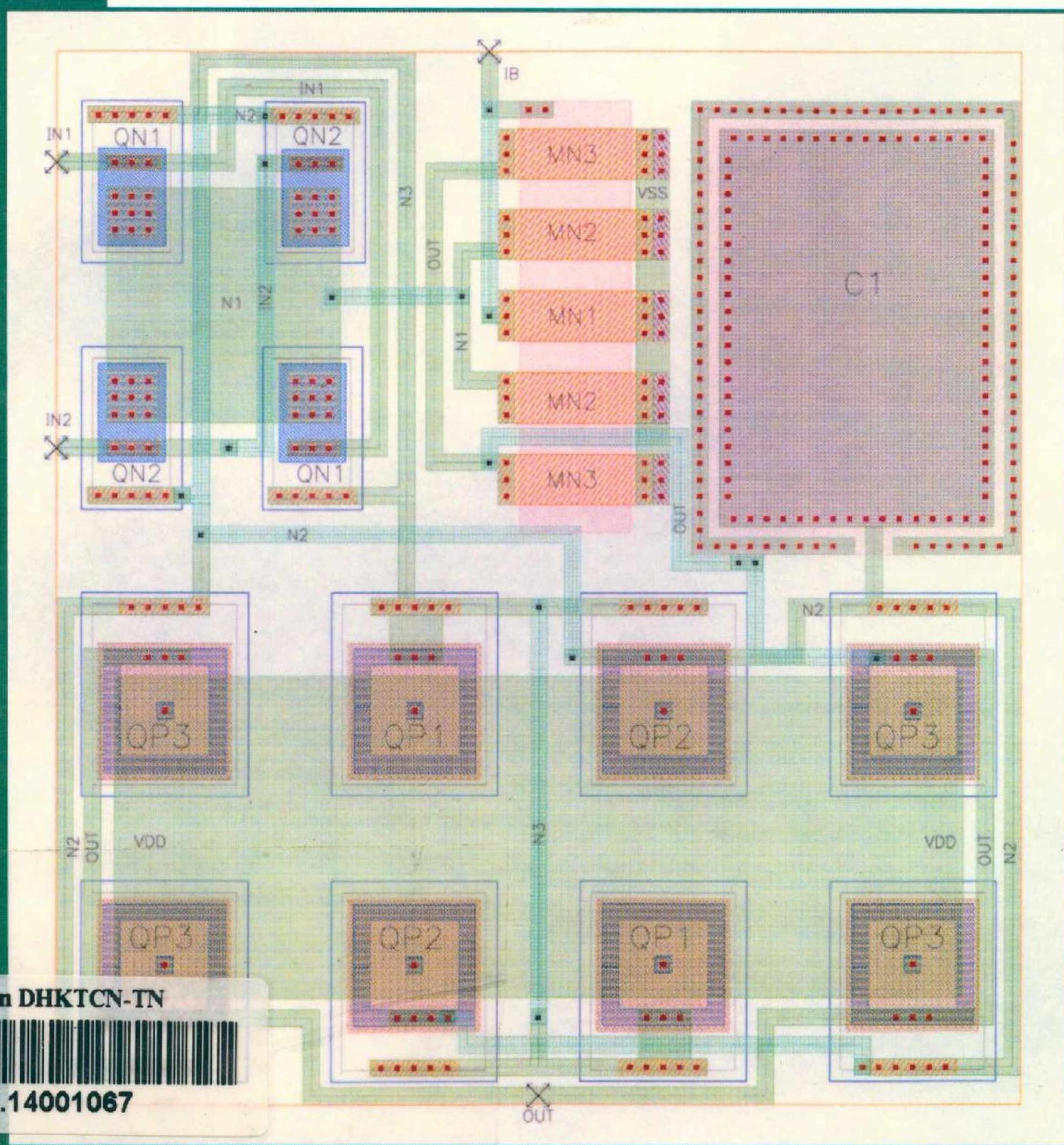


The Art of

ANALOG LAYOUT

Second Edition



Thu Vien DHKTCN-TN



KNV.14001067

Alan Hastings

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The Art of ANALOG LAYOUT
Second Edition

Library of Congress Cataloging-in-Publication Data

On file

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Pearson Prentice Hall
Pearson Education, Inc.
Upper Saddle River, New Jersey 07458

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Printed in the United States of America

10 9 8 7 6 5 4 3

ISBN 0-13-146410-8

Pearson Education Ltd., *London*
Pearson Education Australia Pty. Ltd., *Sydney*
Pearson Education Singapore, Pte. Ltd.
Pearson Education North Asia Ltd., *Hong Kong*
Pearson Education Canada Inc., *Toronto*
Pearson Educación de México, S.A. de C.V.
Pearson Education—Japan, *Tokyo*
Pearson Education Malaysia, Pte. Ltd.
Pearson Education, Inc., Upper Saddle River, New Jersey

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